

## MM54HC139, MM74HC139

### *Dual 2-To-4 Line Decoder*

This decoder utilizes advanced silicon-gate CMOS technology, and is well suited to memory address decoding or data routing applications. It possesses the high noise immunity and low power consumption usually associated with CMOS circuitry, yet has speeds comparable to low power Schottky TTL logic.

The MM54HC139/MM74HC139 contain two independent one-of-four decoders each with a single active low enable input (G1, or G2). Data on the select inputs (A1, and B1 or A2, and B2) cause one of the four normally high outputs to go low.

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### **Rochester Electronics Manufactured Components**

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

### **Quality Overview**

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
  - Class Q Military
  - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
  - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

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*The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.*

## MM54HC139/MM74HC139 Dual 2-To-4 Line Decoder

### General Description

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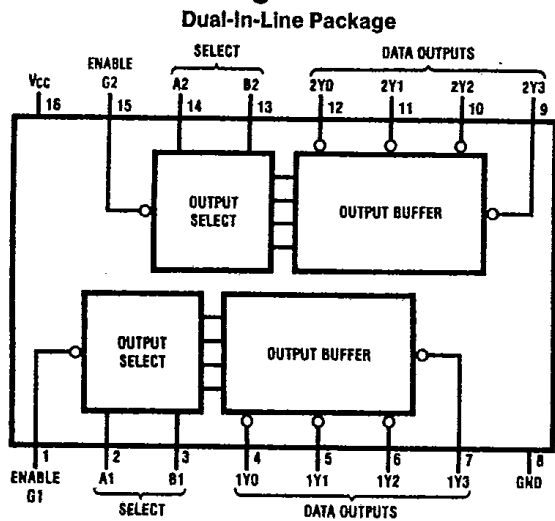
The decoder's outputs can drive 10 low power Schottky TTL equivalent loads, and are functionally as well as pin equivalent

to the 54LS139/74LS139. All inputs are protected from damage due to static discharge by diodes to VCC and ground.

### Features

- Typical propagation delays —
  - Select to outputs (4 delays): 18 ns
  - Select to output (5 delays): 28 ns
  - Enable to output: 20 ns
- Low power: 40  $\mu$ W quiescent supply power
- Fanout of 10 LS-TTL devices
- Input current maximum 1  $\mu$ A, typical 10 pA

### Connection Diagram

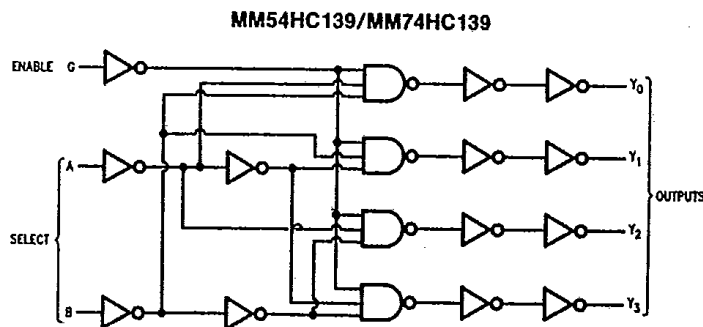


TL/F/5311-1

Order Number MM54HC139\* or MM74HC139\*

\*Please look into Section 8, Appendix D for availability of various package types.

### Logic Diagram



(1 of 2)

TL/F/5311-2

### Truth Table

Inputs			Outputs			
Enable	Select		Y0	Y1	Y2	Y3
G	B	A				
H	X	X	H	H	H	H
L	L	L	L	H	H	H
L	L	H	H	L	H	H
L	H	L	H	H	L	H
L	H	H	H	H	H	L

H = high level, L = low level, X = don't care

**Absolute Maximum Ratings** (Notes 1 & 2)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage ( $V_{CC}$ )	-0.5 to +7.0V
DC Input Voltage ( $V_{IN}$ )	-1.5 to $V_{CC} + 1.5V$
DC Output Voltage ( $V_{OUT}$ )	-0.5 to $V_{CC} + 0.5V$
Clamp Diode Current ( $I_{IK}, I_{OK}$ )	$\pm 20$ mA
DC Output Current, per pin ( $I_{OUT}$ )	$\pm 25$ mA
DC $V_{CC}$ or GND Current, per pin ( $I_{CC}$ )	$\pm 50$ mA
Storage Temperature Range ( $T_{STG}$ )	-65°C to +150°C
Power Dissipation ( $P_D$ ) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. ( $T_L$ ) (Soldering 10 seconds)	260°C

**Operating Conditions**

	Min	Max	Units
Supply Voltage ( $V_{CC}$ )	2	6	V
DC Input or Output Voltage ( $V_{IN}, V_{OUT}$ )	0	$V_{CC}$	V
Operating Temp. Range ( $T_A$ )			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times ( $t_r, t_f$ )			
$V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

**DC Electrical Characteristics** (Note 4)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$		74HC $T_A = -40$ to $85^\circ C$		54HC $T_A = -55$ to $125^\circ C$		Units
				Typ	Guaranteed Limits					
$V_{IH}$	Minimum High Level Input Voltage		2.0V		1.5	1.5	1.5		V	
			4.5V		3.15	3.15	3.15	V		
			6.0V		4.2	4.2	4.2	V		
$V_{IL}$	Maximum Low Level Input Voltage**		2.0V		0.5	0.5	0.5	V		
			4.5V		1.35	1.35	1.35	V		
			6.0V		1.8	1.8	1.8	V		
$V_{OH}$	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 20 \mu A$	2.0V	2.0	1.9	1.9	1.9	V		
			4.5V	4.5	4.4	4.4	4.4	V		
			6.0V	6.0	5.9	5.9	5.9	V		
		$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 4.0$ mA $ I_{OUT}  \leq 5.2$ mA	4.5V	4.2	3.98	3.84	3.7	V		
			6.0V	5.7	5.48	5.34	5.2	V		
$V_{OL}$	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 20 \mu A$	2.0V	0	0.1	0.1	0.1	V		
			4.5V	0	0.1	0.1	0.1	V		
			6.0V	0	0.1	0.1	0.1	V		
		$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 4.0$ mA $ I_{OUT}  \leq 5.2$ mA	4.5V	0.2	0.26	0.33	0.4	V		
			6.0V	0.2	0.26	0.33	0.4	V		
$I_{IN}$	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		$\pm 0.1$	$\pm 1.0$	$\pm 1.0$	$\mu A$		
$I_{CC}$	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		8.0	80	160	$\mu A$		

**Note 1:** Absolute Maximum Ratings are those values beyond which damage to the device may occur.

**Note 2:** Unless otherwise specified all voltages are referenced to ground.

**Note 3:** Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

**Note 4:** For a power supply of  $5V \pm 10\%$  the worst case output voltages ( $V_{OH}$ , and  $V_{OL}$ ) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case  $V_{IH}$  and  $V_{IL}$  occur at  $V_{CC} = 5.5V$  and 4.5V respectively. (The  $V_{IH}$  value at 5.5V is 3.85V.) The worst case leakage current ( $I_{IN}$ ,  $I_{CC}$ , and  $I_{OZ}$ ) occur for CMOS at the higher voltage and so the 6.0V values should be used.

\*\* $V_{IL}$  limits are currently tested at 20% of  $V_{CC}$ . The above  $V_{IL}$  specification (30% of  $V_{CC}$ ) will be implemented no later than Q1, CY'89.

### AC Electrical Characteristics

$V_{CC} = 5V, T_A = 25^\circ C, C_L = 15 \text{ pF}, t_r = t_f = 6 \text{ ns}$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Binary Select to any Output 4 levels of delay		18	30	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Binary Select to any Output 5 levels of delay		28	38	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Enable to any Output		19	30	ns

### AC Electrical Characteristics $C_L = 50 \text{ pF}, t_r = t_f = 6 \text{ ns}$ (unless otherwise specified)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$		74HC	54HC	Units
						$T_A = -40 \text{ to } 85^\circ C$	$T_A = -55 \text{ to } 125^\circ C$	
				Typ	Guaranteed Limits			
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay Binary Select to any Output 4 levels of delay	(Note 6)	2.0V	110	175	219	254	ns
			4.5V	22	35	44	51	ns
			6.0V	18	30	38	44	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay Binary Select to any Output 5 levels of delay	(Note 7)	2.0V	165	220	275	320	ns
			4.5V	33	44	55	64	ns
			6.0V	28	38	47	54	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay Enable to any Output		2.0V	115	175	219	254	ns
			4.5V	23	35	44	51	ns
			6.0V	19	30	38	44	ns
$t_{TLH}, t_{TLH}$	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
$C_{IN}$	Maximum Input Capacitance			3	10	10	10	pF
$C_{PD}$	Power Dissipation Capacitance (Note 5)	(Note 5)		75				pF

**Note 5:**  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .

**Note 6:** 4 levels of delay are A to Y1, Y3 and B to Y2, Y3.

**Note 7:** 5 levels of delay are A to Y0, Y2 and B to Y0, Y1.